

# PMF63UNE 20 V, N-channel Trench MOSFET 20 April 2016

**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	2.2	Α
Static characte	Static characteristics						,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 2 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	57	65	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	□ 3	D I
2	S	souce		
3	D	drain	1 2 SC-70 (SOT323)	G S 017aaa255

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF63UNE	SC-70	plastic surface-mounted package; 3 leads	SOT323			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMF63UNE	Z%V

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	2.2	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	2	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	1.3	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	8	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	300	mW
			[1]	-	395	mW
		T <sub>sp</sub> = 25 °C		-	1.8	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.37	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

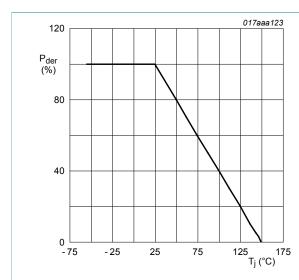


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

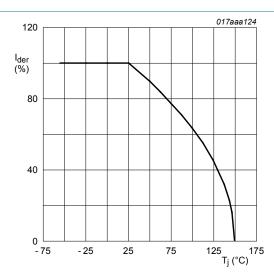


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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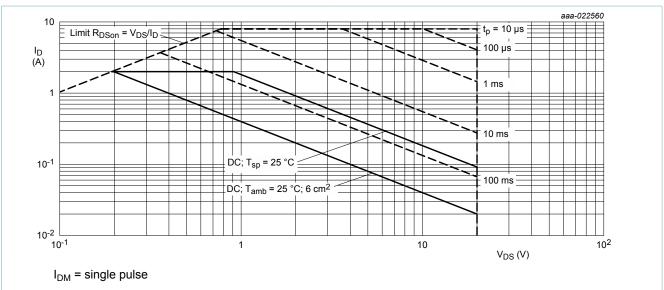


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fro	thermal resistance		[1]	-	363	418	K/W
	from junction to ambient		[2]	-	276	317	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	238	273	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	60	69	K/W

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper; tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

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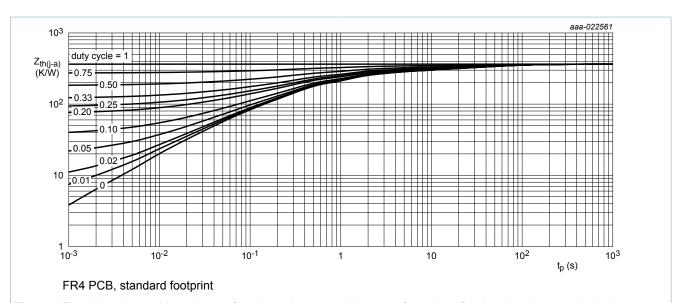


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

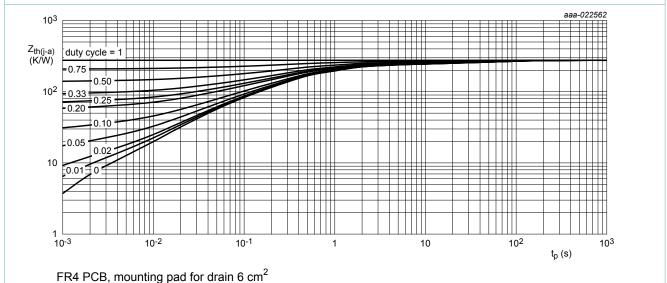


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 ^{\circ}C$	0.45	0.7	1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; $I_{D}$ = 2 A; $T_{j}$ = 25 °C	-	57	65	mΩ
resistance	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 2 A; T <sub>j</sub> = 150 °C	-	84	96	mΩ
		$V_{GS}$ = 2.5 V; $I_D$ = 1.8 A; $T_j$ = 25 °C	-	64	74	mΩ
		$V_{GS}$ = 1.8 V; $I_D$ = 0.8 A; $T_j$ = 25 °C	-	78	88	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$	-	9	-	S
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	1.8	-	Ω
Dynamic ch	naracteristics					_
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; $I_{D}$ = 2 A; $V_{GS}$ = 4.5 V;	-	3.9	5.85	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.3	-	nC
$Q_{GD}$	gate-drain charge		-	0.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	289	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	51	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	42	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	27	-	ns
$t_{d(off)}$	turn-off delay time		-	35	-	ns
t <sub>f</sub>	fall time		-	19	-	ns
Source-drai	in diode				·	
$V_{SD}$	source-drain voltage	$I_S = 0.37 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V
		<u> </u>		_		

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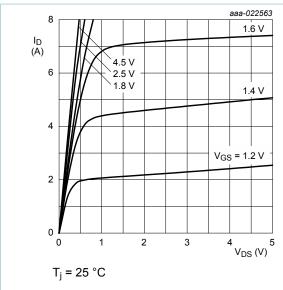


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

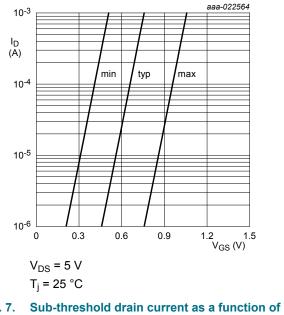


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

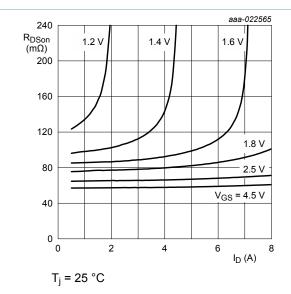


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

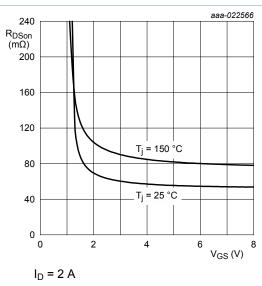


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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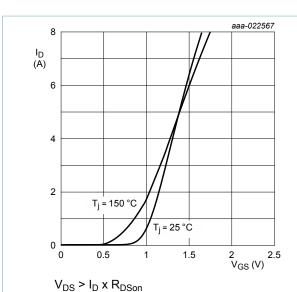


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

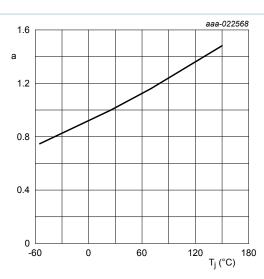


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

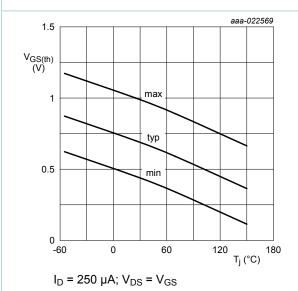


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

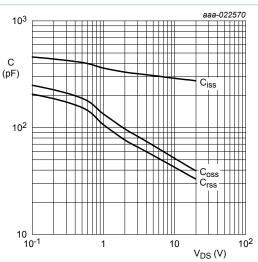


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $f = 1 MHz; V_{GS} = 0 V$ 

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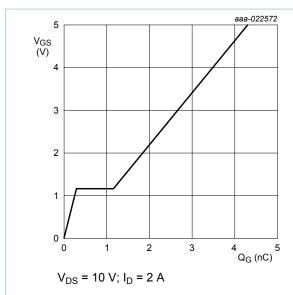


Fig. 14. Gate-source voltage as a function of gate charge; typical values

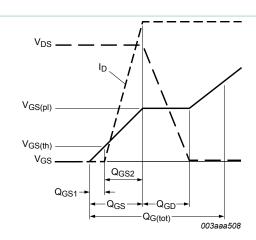


Fig. 15. Gate charge waveform definitions

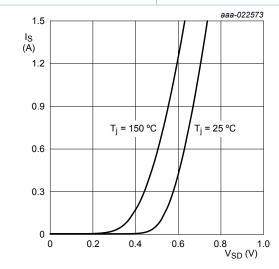
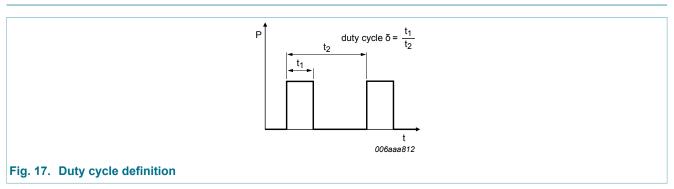


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



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# 12. Package outline

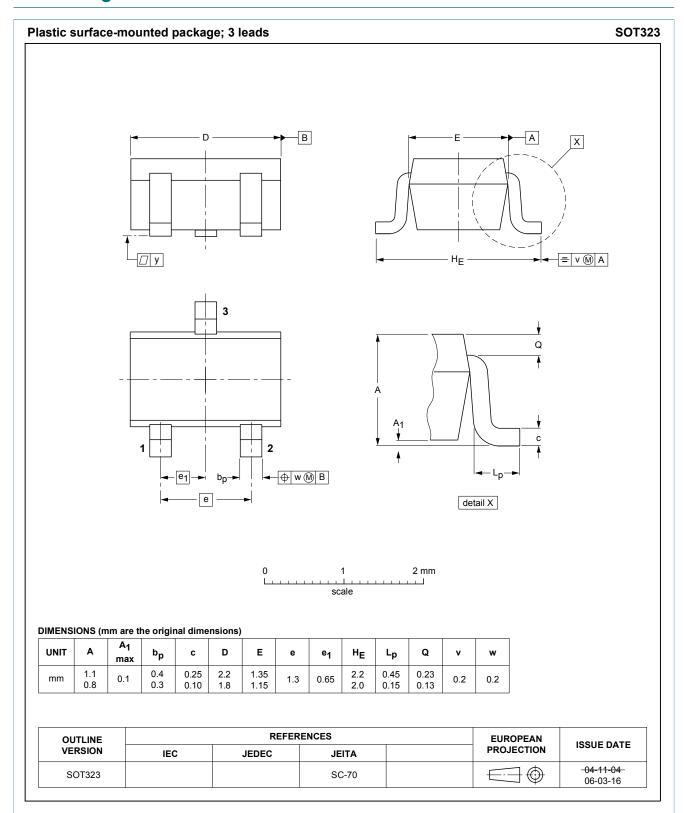


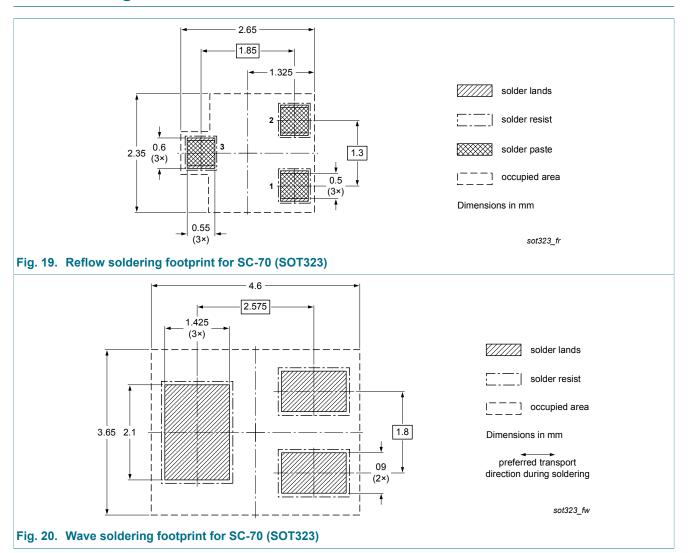
Fig. 18. Package outline SC-70 (SOT323)

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## 20 V, N-channel Trench MOSFET

## 13. Soldering



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# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF63UNE v.1	20160420	Product data sheet	-	-

#### 20 V, N-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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